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Supplementary information:

Controllable Synthesis of Single Crystal SnO₂ Nanowires and Tri-crystal SnO₂ Nanobelts

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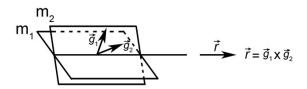


Fig. S1. Schematic illustration of determining the growth direction of NWs. g_1 and g_2 represent two reciprocal vectors perpendicular to the NW side-edge (axial direction), and r indicates the growth (axial) direction of the NW.

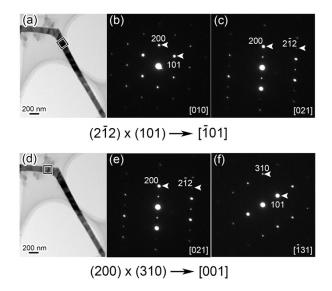


Fig. S2. The growth direction of single crystal nanowires, along from $[\overline{1}01]$ to [001].

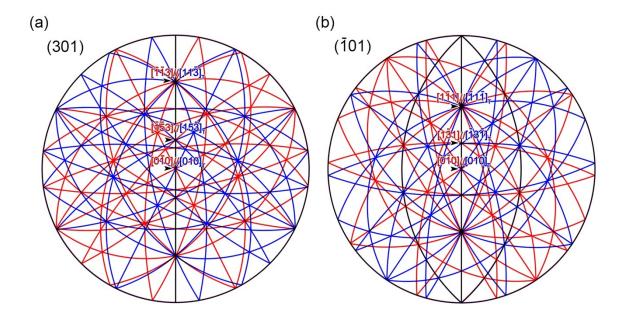


Fig. S3. (a-b) Calculated superposition stereographic projections of the Kikuchi patterns corresponding to (301) and $(\overline{1}01)$ twins.

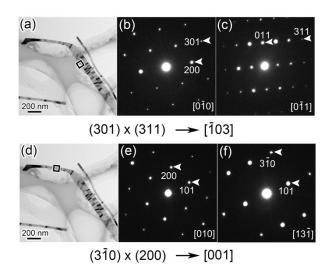


Fig. S4. The growth direction of tri-crystal nanobelts, along from $[\overline{1}03]$ to [001].

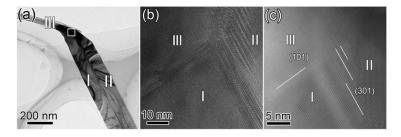


Fig. S5. (a) BF image of individual tri-crystal SnO_2 of type Π . (b) The boundary of tri-crystal with a lot of defects. (c) STEM image of the tri-crystal boundary.

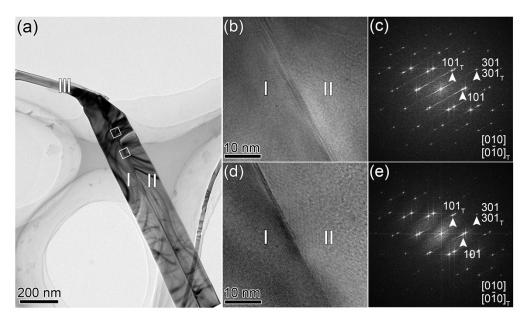


Fig. S6. (a) BF image of individual tri-crystal SnO_2 of type Π . (b-c) The HRTEM image from upper rectangular area in (a) and FFT pattern corresponding to (b). (d-e) The HRTEM image from lower rectangular area in (a) and FFT pattern corresponding to (c).

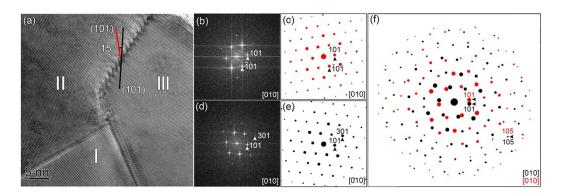


Fig. S7. (a) The HRTEM image of tri-crystal boundary. Part Π clockwise rotation 15 degrees can coincide with Part III. (b-e) FFT image from part Π and part III and corresponding simulated SAED patterns. (f) The superposition of (c) and (e) FFT simulations.